

N-Channel 80 V (D-S) MOSFET

DESCRIPTION

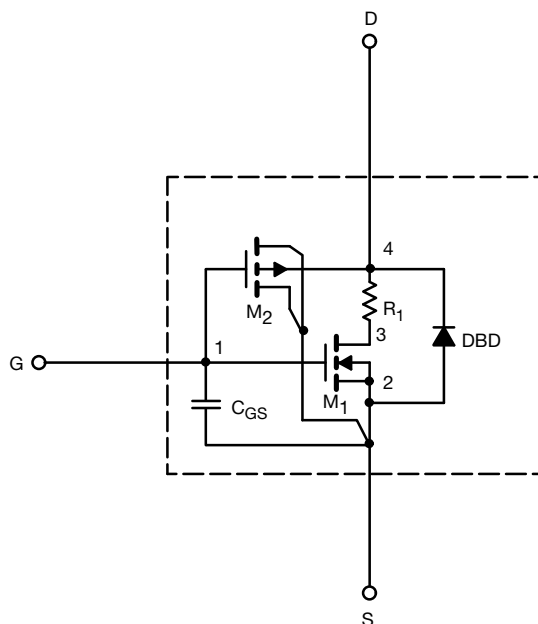
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



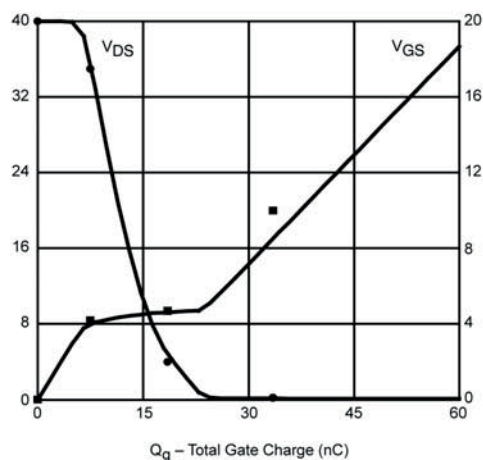
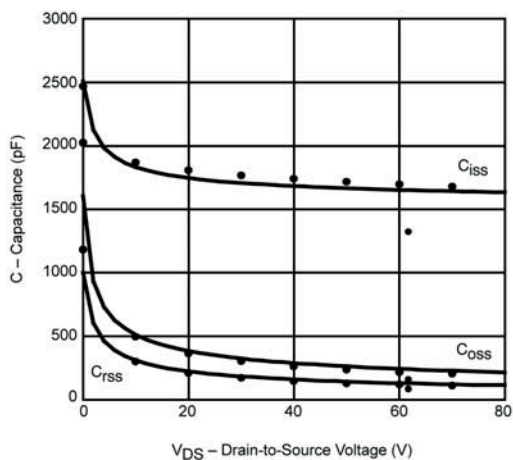
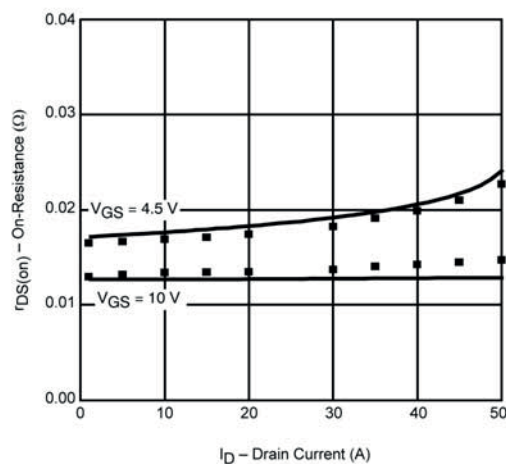
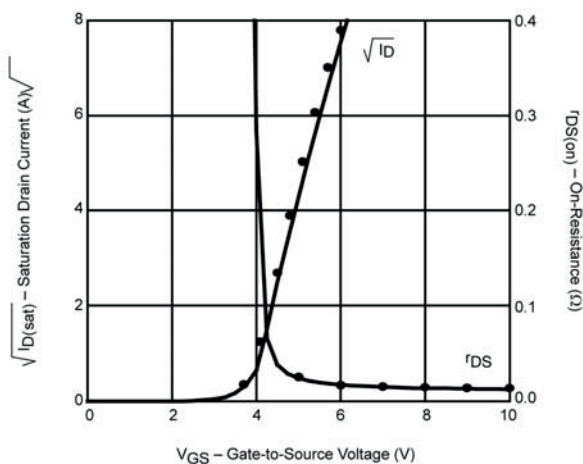
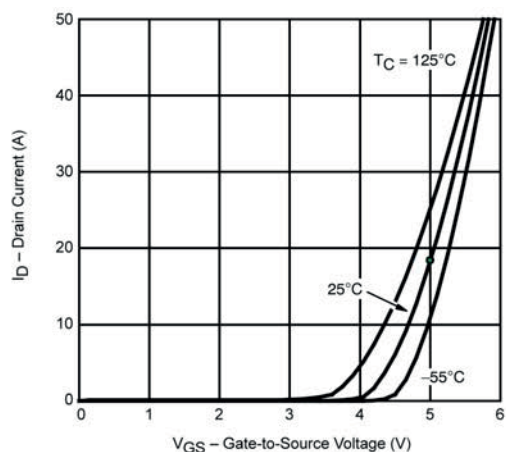
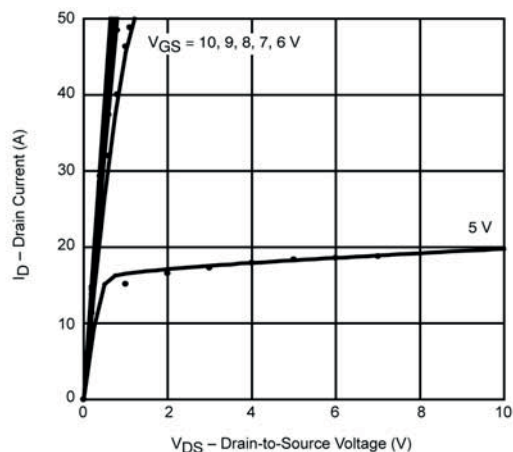
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2.6	-	V
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	319	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$	0.0127	0.0135	Ω
		$V_{GS} = 6\ \text{V}$, $I_D = 8\ \text{A}$	0.0175	0.0175	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 10\ \text{A}$	24	25	S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.8\ \text{A}$, $V_{GS} = 0\ \text{V}$	0.83	0.75	V
Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 40\ \text{V}$, $V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$	37	34	nC
Gate-Source Charge	Q_{gs}		7.5	7.5	
Gate-Drain Charge	Q_{gd}		11	11	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 40\ \text{V}$, $R_L = 40\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_g = 6\ \Omega$	18	17	ns
Rise Time	t_r		22	11	
Turn-Off Delay Time	$t_{d(off)}$		30	40	
Fall Time	t_f		45	31	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.8\ \text{A}$, $dI/dt = 100\ \text{A}/\mu\text{s}$	40	45	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\ \%$.
b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25^\circ\text{C}$, unless otherwise noted)



Note

- Dots and squares represent measured data.

Copyright: Vishay Intertechnology, Inc.